

Our Docket No.: 5882P067
Express Mail No.: EV339913157US

UTILITY APPLICATION FOR UNITED STATES PATENT
FOR
VARIABLE GAIN AMPLIFIER

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VARIABLE GAIN AMPLIFIER

BACKGROUND OF THE INVENTION

Field of the Invention

The present invention relates to a CMOS variable gain amplifier (VGA), which can provide a function of controlling a gain of input signals with both low distortion and high-speed operating range, by allowing the amplifier to have a variable gain by controlling the value of an output current of its drain terminal against a gate voltage of the NMOS transistor, can control a voltage gain with a wide gain control range and can be embedded in the IC.

Background of the Related Art

Performance parameters of VGA that must be considered in designing the CMOS variable gain amplifier may include maximum of signal-to-noise ratio (SNR) for a desired signal value, a frequency bandwidth, low distortion, the input signal level that guarantees desired linearity, noise characteristics, gain control range, and the like. Further, its dependence on the temperature variation or supply voltage can not be excluded. In particular, it is not easy to design a CMOS VGA circuit having the operating frequency range of over 100 MHz in view of device technology characteristics. Furthermore, due to limitations in reduction of the threshold voltage in the MOS device, the input/output signal level is

limited. It is, thus, difficult to expect a smooth operation of VGA for a low power supply because of smaller input signal range.

Therefore, it is difficult to implement the CMOS variable gain amplifier with a low power consumption characteristics at the low voltage as an integrated circuit.

SUMMARY OF THE INVENTION

Accordingly, the present invention has been made in view of the above problems, and it is an object of the present invention is to provide a CMOS variable gain amplifier that provides a function of variable gain for a large input signal range according to the control voltage at a low supply voltage and has a wideband characteristic.

Another object of the present invention is to provide a CMOS variable gain amplifier with low power consumption, that can be implemented as IC.

Additional advantages, objects, and features of the invention will be set forth in part in the description which follows and in part will become apparent to those having ordinary skill in the art upon examination of the following or may be learned from practice of the invention. The objectives and other advantages of the invention may be realized and attained by the structure particularly pointed out in the written description and claims hereof as well as the appended drawings.

To achieve the above objects, according to the present invention, there is provided a variable gain amplifier, including a voltage-current

converter for converting voltages of a wide range into currents, a current shared circuit for receiving the currents from the voltage-current converter and controlling values of output currents depending on first and second control voltages, and a current-voltage converter for converting the output currents from the current shared circuit into differential voltages depending on a bias voltage in order to obtain a variable gain.

In another aspect of the present invention, it is to be understood that both the foregoing general description and the following detailed description of the present invention are exemplary and explanatory and are intended to provide further explanation of the invention as claimed.

BRIEF DESCRIPTION OF THE DRAWINGS

The above and other objects, features and advantages of the present invention will be apparent from the following detailed description of the preferred embodiments of the invention in conjunction with the accompanying drawings, in which:

FIG. 1 is a block diagram illustrating a basic construction of a CMOS variable gain amplifier according to the present invention,

FIG. 2 is a circuit diagram illustrating the construction of a CMOS variable gain amplifier according to one embodiment of the present invention,

FIG. 3 is a circuit diagram illustrating the construction of a CMOS variable gain amplifier according to another embodiment of the present invention, and

FIG. 4 is a circuit diagram illustrating the construction of a CMOS variable gain amplifier according to still another embodiment of the present invention.

DETAILED DESCRIPTION OF THE EMBODIMENTS

Reference will now be made in detail to the preferred embodiments of the present invention, examples of which are illustrated in the accompanying drawings, in which like reference numerals are used to identify the same or similar parts.

FIG. 1 is a block diagram illustrating a basic construction of a CMOS variable gain amplifier according to the present invention.

As shown in FIG. 1, the CMOS variable gain amplifier includes a voltage-current (V-I) converter **11** for converting the input voltages (V_{in+} and V_{in-}) into currents, a current shared circuit **12** for receiving the converted currents from the voltage-current converter **11** as an input and controlling its transconductance depending on control voltages (V_{c+} and V_{c-}) to control the value of the current, and a current-voltage (I-V) converter **13** for converting the currents inputted from the current shared circuit **12** into voltages depending on a bias voltage (V_b).

FIG. 2 is a circuit diagram illustrating the construction of a CMOS variable gain amplifier according to one embodiment of the present invention. The construction of the CMOS variable gain amplifier will now be described with reference to FIG. 1.

The voltage-current converter **11** has first and second resistors **R21**

and **R22**. The first resistor **R21** is connected between the first input voltage **V_{in+}** terminal and a first node **Q21**, and the second resistor **R22** is connected between the second input voltage **V_{in-}** terminal and a second node **Q22**.

The current shared circuit 12 includes first and second NMOS transistors **N21** and **N22** driven by the first control voltage **V_{c+}** and third and fourth NMOS transistors **N23** and **N24** driven by the second control voltage **V_{c-}**. The current shared circuit 12 controls the output current values of the drain terminals against the gate voltages of the first ~ fourth NMOS transistors **N21 ~ N24**. The first NMOS transistor **N21** is connected between the first node **Q21** and a third node **Q23** and is driven by the first control voltage **V_{c+}**. The second NMOS transistor **N22** is connected between the second node **Q22** and a fourth node **Q24** and is driven by the first control voltage **V_{c+}**. The third NMOS transistor **N23** is connected between the first node **Q21** and the fourth node **Q24** and is driven by the second control voltage **V_{c-}**. The fourth NMOS transistor **N24** is connected between the second node **Q22** and the third node **Q23** and is driven by the second control voltage **V_{c-}**.

The current-voltage converter 13 includes third and fourth resistors **R23** and **R24**, fifth and sixth NMOS transistors **N25** and **N26**, and first and second current sources **I_{s1}** and **I_{s2}**. The third resistor **R23** is connected between the power supply terminal **V_{dd}** and the first output terminal **V_{o+}** and the fourth resistor **R24** is connected between the power supply terminal **V_{dd}** and the second output terminal **V_{o-}**. The fifth NMOS transistor **N25**

driven by the bias voltage **Vb1** is connected between the first output terminal **Vo+** and the third node **Q23**. The sixth NMOS transistor **N26** driven by the bias voltage **Vb1** is connected between the second output terminal **Vo-** and the fourth node **Q24**. Further, the first current source **Is1** is connected between the third node **Q23** and the ground terminal **Vss**. The second current source **Is2** is connected between the fourth node **Q24** and the ground terminal **Vss**.

The method of driving the variable gain amplifier constructed above according to the present invention will be below described.

The first and second input voltages **Vin+** and **Vin-** are converted into the currents by the first and second resistors **R21** and **R22** constituting the voltage-current converter **11**. These currents are then supplied to the current shared circuit **12**.

In the current shared circuit **12**, the first ~ fourth NMOS transistors **N21**, **N22**, **N23** and **N24** have a double balance source coupled pair shape. A variable output current is obtained by controlling transconductance in the triode region by means of the control voltages **Vc+** and **Vc-** each applied to the gate terminals of the transistors. The current flowing into the drain terminal of each of the transistors can be expressed into the following [Mathematical Equation 1] ~ [Mathematical Equation 4].

[Equation 1]

$$I_{N21} = K \left[\left(V_{GS} + \frac{V_c}{2} - V_{TH} \right) \left(\frac{V_{in}}{2} \right) - \frac{1}{2} \left(\frac{V_{in}}{2} \right)^2 \right]$$

[Equation 2]

$$I_{N22} = K \left[\left(V_{GS} + \frac{V_c}{2} - V_{TH} \right) \left(-\frac{V_{in}}{2} \right) - \frac{1}{2} \left(-\frac{V_{in}}{2} \right)^2 \right]$$

【Equation 3】

$$I_{N23}=K\left[\left(V_{GS}-\frac{V_c}{2}-V_{TH}\right)\left(\frac{V_{in}}{2}\right)-\frac{1}{2}\left(\frac{V_{in}}{2}\right)^2\right]$$

【Equation 4】

$$I_{N24}=K\left[\left(V_{GS}+\frac{V_c}{2}-V_{TH}\right)\left(-\frac{V_{in}}{2}\right)-\frac{1}{2}\left(-\frac{V_{in}}{2}\right)^2\right]$$

wherein $v_c = (V_{c+}) - (V_{c-})$, $K = \mu C_{OX} (W/L)$, V_{TH} is the threshold voltage of the transistor.

Therefore, the differential output current that is applied from the current shared circuit 12 to the current-voltage converter 13 at the next stage is same to [Equation 5]. This output current is converted into the output voltage V_o by the load at the output stage.

【Equation 5】

$$I_O = I_{N21} + I_{N24} - I_{N22} - I_{N23}$$

Further, a condition where respective transistors operate in the triode region can be expressed into the following [Mathematical Equation 6].

【Equation 6】

$$V_{GS} > V_{TH}, V_{GS} - V_{TH} > V_{DS}$$

wherein V_{GS} is a gate-source voltage of each of the transistors and V_{DS} is a drain-source voltage of each of the transistors.

The current-voltage converter 13 converts the variable current inputted from the current shared circuit 12 into the output voltage. The current bias is decided by the first and second current sources I_{s1} and I_{s2} . This is closely related to the linearity and the driving capability of the variable gain amplifier. The fifth and sixth NMOS transistors N25 and N26 for inputting the bias voltage V_{b1} as the gate voltage to a current

applied as a current inputted type in order to operate the bias voltage **Vb1** in a stabilized DC bias level, serve to stabilize the common mode voltage at the output stage of the variable gain amplifier.

FIG. 3 is a circuit diagram illustrating the construction of a CMOS variable gain amplifier according to another embodiment of the present invention, in which the resistors of the current-voltage converter in FIG. 2 are replaced with a differential source follower circuit having MOS transistors in order to accomplish a wide range of an input signal that guarantees the linearity in the DC bias. It is required that the differential source follower circuit be implemented sufficiently considering the value of source impedance. The construction of the differential source follower circuit will be described below.

A voltage-current converter **11** includes a differential source follower having first and second NMOS transistors **N301** and **N302** for differentially receiving the input voltages and first and second current sources **Is1** and **Is2**. The first NMOS transistor **N301** is connected between the power supply terminal **Vdd** and a first node **Q31** and is driven by a first input voltage **Vin+**. The second NMOS transistor **N302** is connected between the power supply terminal **Vdd** and a second node **Q32** and is driven by a second input voltage **Vin-**. The first current source **Is1** is connected between the first node **Q31** and a ground terminal **Vss**, and a second current source **Is2** is connected between the second node **Q32** and the ground terminal **Vss**.

A current shared circuit **12** includes third and fourth NMOS

transistors **N303** and **N304** driven by a first control voltage **Vc+**, and fifth and sixth NMOS transistors **N305** and **N306** driven by a second control voltage **Vc-**. The third NMOS transistor **N303** is connected between the first node **Q31** and a third node **Q33** and is driven by the first control voltage **Vc+**. The fourth NMOS transistor **N304** is connected between the second node **Q32** and a fourth node **Q34** and is driven by the first control voltage **Vc+**. The fifth NMOS transistor **N305** is connected between the first node **Q31** and the fourth node **Q34** and is driven by the second control voltage **Vc-**. The sixth NMOS transistor **N306** is connected between the second node **Q32** and the third node **Q33** and is driven by the second control voltage **Vc-**.

A current-voltage converter **13** includes first and second resistors **R31** and **R32**, seventh and eighth NMOS transistors **N307** and **N308** driven by a first bias voltage **Vb1**, and ninth and tenth NMOS transistors **N309** and **N310** driven by a second bias voltage **Vb2**. The first resistor **R31** is connected between the power supply terminal **Vdd** and the first output terminal **Vo+**. The second resistor **R32** is connected between the power supply terminal **Vdd** and the second output terminal **Vo-**. The seventh NMOS transistor **N307** driven by the first bias voltage **Vb1** is connected between the first output terminal **Vo+** and the third node **Q33**. The eighth NMOS transistor **N308** driven by the first bias voltage **Vb1** is connected between the second output terminal **Vo-** and the fourth node **Q34**. Further, the ninth NMOS transistor **N309** driven by the second bias voltage **Vb2** is connected between the third node **Q33** and the ground terminal **Vss**. The

tenth NMOS transistor **N310** driven by the second bias voltage **Vb2** is connected between the fourth node **Q34** and the ground terminal **Vss**.

In the voltage-current converter **11** of the variable gain amplifier constructed above according to the present invention, the currents outputted through the first and second nodes **Q31** and **Q32** are decided by the first and second NMOS transistors **N301** and **N302** for differentially receiving the first and second input voltages **Vin+** and **Vin-** and the first and second current sources **Is1** and **Is2** each connected to the source terminals of the first and second NMOS transistors **N301** and **N302**.

FIG. 4 is a circuit diagram illustrating the construction of a CMOS variable gain amplifier according to a still another embodiment of the present invention in which the output load having the resistors in FIG. 3 is replaced with an active load circuit. The construction of the CMOS variable gain amplifier will now be described in detail.

A voltage-current converter **11** has a differential source follower including first and second NMOS transistors **N401** and **N402** for differentially receiving the input voltages and first and second current sources **Is1** and **Is2**. The first NMOS transistor **N401** is connected between a power supply terminal **Vdd** and a first node **Q41** and is driven by a first input voltage **Vin+**. The second NMOS transistor **N402** is connected between the power supply terminal **Vdd** and a second node **Q42** and is driven by a second input voltage **Vin-**. The first current source **Is1** is connected between the first node **Q41** and a ground terminal **Vss**. The second current source **Is2** is connected between the second node **Q42** and

the ground terminal V_{ss} .

A current shared circuit 12 includes third and fourth NMOS transistors **N403** and **N404** driven by a first control voltage V_{c+} and fifth and sixth NMOS transistors **N405** and **N406** driven by a second control voltage V_{c-} . The third NMOS transistor **N403** is connected between the first node **Q41** and a third node **Q43** and is driven by the first control voltage V_{c+} . The fourth NMOS transistor **N404** is connected between the second node **Q42** and a fourth node **Q44** and is driven by the first control voltage V_{c+} . The fifth NMOS transistor **N405** is connected between the first node **Q41** and the fourth node **Q44** and is driven by the second control voltage V_{c-} . The sixth NMOS transistor **N406** is connected between the second node **Q42** and the third node **Q43** and is driven by the second control voltage V_{c-} .

A current-voltage converter 13 includes first and second active loads 41 and 42, seventh and eighth NMOS transistors **N407** and **N408** driven by a first bias voltage V_{b1} , and ninth and tenth NMOS transistors **N409** and **N410** driven by a second bias voltage V_{b2} . In the above, the first active load 41 connected between a power supply terminal V_{dd} and a first output terminal V_{o+} includes a first PMOS transistor **P401** connected between the power supply terminal V_{dd} and a fifth node **Q45** and driven by the potential of a sixth node **Q46**, an eleventh NMOS transistor **N411** connected between the power supply terminal V_{dd} and the sixth node **Q46** and driven by the potential of a fifth node **Q45**, and a third current source I_{s3} and a first capacitor **C401** connected in parallel between the sixth node

Q46 and a ground terminal **Vss**. Further, the second active load **42** connected between the power supply terminal **Vdd** and a second output terminal **Vo-** includes a second PMOS transistor **P402** connected between the power supply terminal **Vdd** and a seventh node **Q47** and driven by the potential of an eighth node **Q48**, a twelfth NMOS transistor **N412** connected between the power supply terminal **Vdd** and the eighth node **Q48** and driven by the potential of the seventh node **Q47**, and a fourth current source **Is4** and a second capacitor **C402** connected in parallel between the eighth node **Q48** and the ground terminal **Vss**. The seventh NMOS transistor **N407** driven by the first bias voltage **Vb1** is connected between the first output terminal **Vo+** and the third node **Q43**. The eighth NMOS transistor **N408** driven by the first bias voltage **Vb1** is connected between the second output terminal **Vo-** and the fourth node **Q44**. Furthermore, the ninth NMOS transistor **N409** driven by the second bias voltage **Vb2** is connected between the third node **Q43** and the ground terminal **Vss**. The tenth NMOS transistor **N410** driven by the second bias voltage **Vb2** is connected between the fourth node **Q44** and the ground terminal **Vss**.

In the current-voltage converter **13** of the variable gain amplifier according to still another embodiment of the present invention, the output load is constructed using the active load instead of the resistor. It is thus possible to improve the gain value, and low voltage operation and frequency characteristics. In other words, in FIG. 4, the first and second PMOS transistors **P401** and **P402** can supply a stabilized bias through the eleventh and twelfth NMOS transistors **N411** and **N412** and the third and

fourth current sources **Is3** and **Is4**. Further, the first and second PMOS transistors **P401** and **P402** can have low voltage and high gain and can operated at a wideband range, than the load constructed using the resistor, by improving the frequency characteristic of the first and second capacitors **C401** and **C402**. In other words, a reciprocal number of a transconductance of each of the first and second PMOS transistors **P401** and **P402** become an approximate output load value. This may have a high value even at a voltage range lower than the resistor load, whereby the high gain can be realized. Further, this value is kept in a more stabilized DC voltage level at the output stage through a negative feedback connection of the first and second PMOS transistors **P401** and **P402** and the eleventh and twelfth NMOS transistors **N411** and **N412**. Also, there is an advantage that the variable gain amplifier can operate in a high frequency region using frequency compensation capacitance. The frequency characteristic of the variable gain amplifier according to the present invention is dependent on parasitic capacitance at the load resistor or the drain terminals of the active load PMOS transistors **P401** and **P402**. A good frequency characteristic can be thus accomplished by optimizing the size of a constitutional device.

As described above, according to the present invention, a current shared circuit and additional variable current generating unit and output stage voltage generating circuit are used. Therefore, the present invention has new effects that it can simply implement a CMOS variable gain amplifier having low distortion and high frequency bandwidth

characteristics at a low supply power and minimize the area accordingly, and allows the variable gain amplifier to be embedded in the IC. Further, the present invention has a new effect that it has a low supply voltage or a function of setting a operation mode control if necessary.

The forgoing embodiments are merely exemplary and are not to be construed as limiting the present invention. The present teachings can be readily applied to other types of apparatuses. The description of the present invention is intended to be illustrative, and not to limit the scope of the claims. Many alternatives, modifications, and variations will be apparent to those skilled in the art.